

PT85QWx45 Pulse Power Thyristor Switch

Preliminary Information

DS5334-2 July 2012 (LN 29644)

KEY PARAMETERS

 $\begin{array}{lll} V_{DRM} & 4500V \\ I_{T(AV)} & 1670A \\ I_{TSM} & 37000A \\ dI_{T}/dt & 22000A/\mu s \end{array}$

Outline type code: W (See Package Details for further information)

Fig. 1 Package outline

APPLICATIONS

- Pulse Power
- Crowbars
- Ignitron Replacement

FEATURES

- Double Side Cooling
- Fast Turn-on
- Low Turn-on Losses

VOLTAGE RATINGS

Type Number	Repetitive Peak Off-state Voltage V _{DRM} (V)	Repetitive Peak Reverse Voltage V _{RRM} (V)	Conditions
PT85QWx45	4500	16	$\begin{array}{l} T_{vj} = 0^{\circ}to125^{\circ}C, \\ I_{DRM} = ,\ I_{RRM} = 50mA, \\ V_{DRM},\ V_{RRM}t_{p} = 10ms \end{array}$

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
I _{T(AV)}	Mean on-state current	T _{case} = 80 °C, Half sine 50Hz resistive load	1670	А
I _{T(RMS)}	RMS on-state current	T _{HS} = 80 °C	1225	А



SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non repetitive) on-state current	10ms half sine. T _{case} = 125 ℃	29.6	kA
l ² t	I ² t for fusing	$V_R = 50\% V_{RRM} - \frac{1}{4} sine$	4.38	MA ² s
I _{TSM}	Surge (non repetitive) on-state current	10ms half sine; T _{case} = 125 ℃	37	kA
l ² t	I ² t for fusing	V _R = 0	6.85	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	dc	-	0.01	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 40kN with mounting compound	Double side	-	0.001	°C/W
		On-state (conducting)		-	135	℃
$T_{v_{j}}$	Virtual junction temperature	Reverse (blocking)		-	125	℃
T _{stg}	Rate of rise of reverse gate current			-55	125	∞
-	Clamping force			36.0	44.0	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions		Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} T _{case} = 125 ℃, V _{RG} = 0V		_	250	mA
dV/dt	Maximum linear rate of rise of off- state voltage	To 66% V_{DRM} ; $R_{GK} \le 1.5Ω$, $T_j = 125$ °C		_	200	V/µs
dI/dt	Rate of rise of on-state current	From 67%V _{DRM} to 90kA Gate source 130A t_r 1.5 μ s, T_j =125°C	Non-repetitive	-	22	kA/μs
V _{T(TO)}	Threshold voltage	At T _{vj} = 125 ℃		-	1.45	V
r _T	On-state slope resistance	At T _{vj} = 125 ℃		-	0.3	mΩ

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions	Min.	Max.	Units
V _{GT}	Gate trigger voltage	V _{DRM} = 5V,T _{case} = 25 ℃	1.0	4.0	V
I_{GT}	Gate trigger current	V _{DRM} = 5V,T _{case} = 25 °C	-	1.5	А



ORDERING INFORMATION

PT Pulse Power Thyristor

85Q Device type

W package outline type code x lead length (see table, right)

45 Voltage x 100

Lead length (x)				
О	No lead			
С	8"	200mm		
D	10"	250mm		
Е	12"	300mm		
F	16"	400mm		
G	18"	450mm		
Н	20"	500mm		
J	24"	600mm		
К	30"	750mm		
L	40"	1000mm		

CURVES

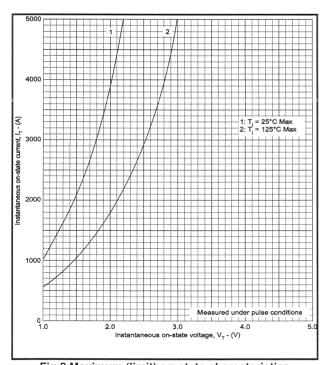


Fig.2 Maximum (limit) on-state characteristics

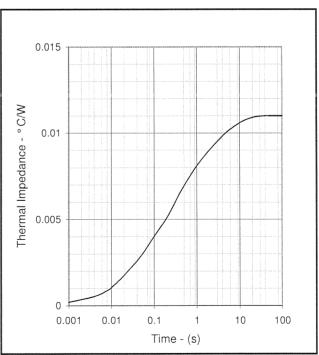


Fig.3 Maximum (limit) transient thermal impedancedouble side cooled



PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

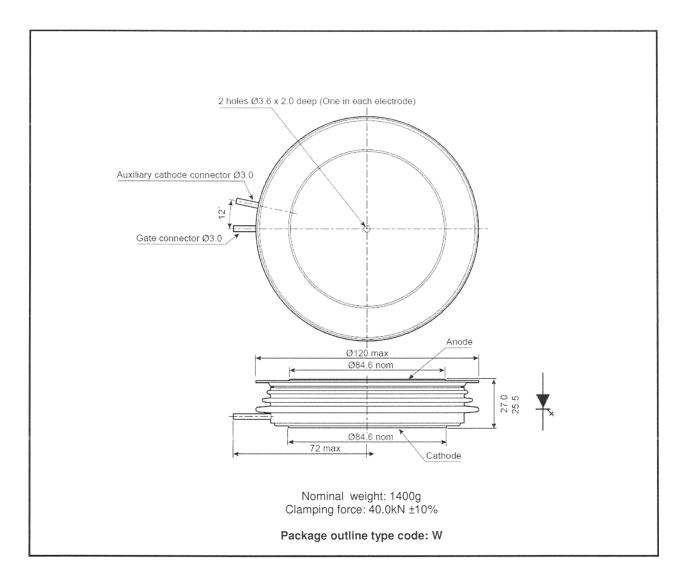


Fig.4 Package outline





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